## **TSMC40: 3.3V GPIO**



#### Libraries

Name	Process Form Factor		
RGO_TSMC40_25V33_LP_50C	LP	Inline CUP	
RGO_TSMC40_25V33_LP_30C	LP	Staggered CUP	

## **Summary**

The 3.3V General Purpose I/O library provides bidirectional I/O, isolated analog I/O, and a full complement of power cells along with corner and spacer cells to assemble a complete pad ring by abutment. An included rail splitter allows multiple power domains to be isolated in the same pad ring while maintaining continuous VDD/VSS for robust ESD protection.

- Programmable bidirectional GPIO
- Input-only buffer
- Isolated analog I/O
- Full complement of power, corner, and spacer cells

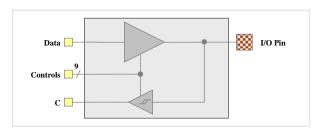
#### **ESD Protection:**

- JEDEC compliant
  - 2KV ESD Human Body Model (HBM)
  - o 200 V ESD Machine Model (MM)
  - 500 V ESD Charge Device Model (CDM)

#### Latch-up Immunity:

- JEDEC compliant
  - o Tested to I-Test criteria of ± 100mA @ 125°C

## SRx\_BI\_SDS\_33V\_STB



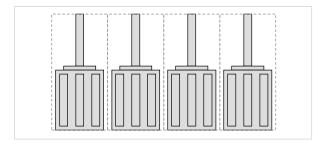
#### **Bidirectional GPIO Driver Features**

- Multi-Voltage (1.8V, 2.5V, 3.3V)
- LVCMOS / LVTTL input with selectable hysteresis
- Programmable drive strength (rated 2mA to 12mA)
- Selectable output slew rate
- Optimized for EMC with SSO factor of 8
- Open-drain output mode
- Programmable input options (pull-up/pull-down/repeater)
- Power-On Start (POS) capable
- Power sequencing independent design with Power-On Control
- Fault tolerant cell provides fail-safe operation

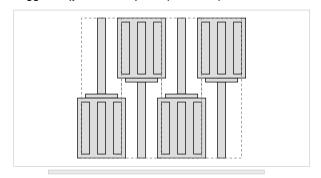
In full-drive mode, this driver can operate to frequencies in excess of 100MHz with 15pF external load and 125 MHz with 10pF load. Actual frequency limits are load and system dependent. A maximum of 200 MHz can be achieved under small capacitive loads.

## **Cell Sizes & Form Factor**

## Inline (core-limited) - 50 µm x 120 µm



#### Staggered (pad-limited) - 30µm x 180µm



## **Recommended operating conditions**

	Description	Min	Nom	Max	Units
$V_{VDD}$	Core supply voltage	0.99	1.1	1.21	V
V <sub>DVDD</sub>		2.97	3.3	3.63	V
	I/O supply voltage	2.25	2.5	2.50	V
		1.62	1.8	1.98	V
TJ	Junction temperature	-40	25	125	°C
$V_{PAD}$	Voltage at PAD	0	-	V <sub>DVDD</sub>	V

### **Characterization Corners**

Nominal VDD	Model	VDD	DVDD <sup>[1]</sup>	Temperature
1.1	FF	+10%	+10%	-40°C
	FF	+10%	+10%	0°C
	FF	+10%	+10%	125°C
	TT	nominal	nominal	25°C
	SS	-10%	-10%	-40°C
	SS	-10%	-10%	0°C
	SS	-10%	-10%	125°C

[1] DVDD = 1.8, 2.5 and 3.3V

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